MSKSEMI 美森科
SEMICONDUCTOR

ESD TVS TSS MOV GDT PLED

AONR36366-MS

Product specification

Description

The AONR36366-MS uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

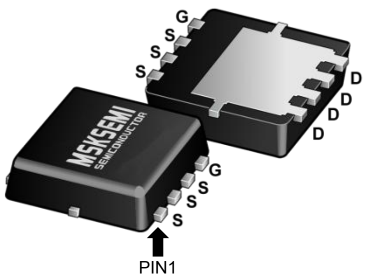
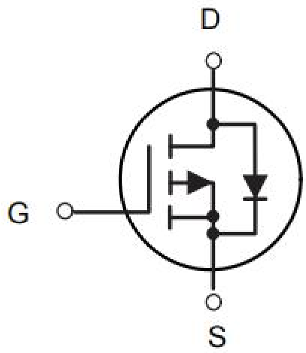
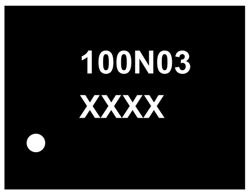
Features

- V_{DS} = 30V I_D =100A
- $R_{DS(ON)}$ < 5 . 5 mΩ @ V_{GS}=10V

Application

- Battery protection
- Load switch
- Uninterruptible power supply

Reference News

PACKAGE OUTLINE	P-Channel MOSFET	Marking
		
DFN3X3-8L		

Absolute Maximum Ratings (TC=25℃ unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25˚C	Continuous Drain Current, V_{GS} @ 10V[1]	100	A
I_D@T_C=100˚C	Continuous Drain Current, V_{GS} @ 10V[1]	70	A
I_D@T_A=25˚C	Continuous Drain Current, V_{GS} @ 10V[1]	30	A
I_D@T_A=70˚C	Continuous Drain Current, V_{GS} @ 10V[1]	25	A
I_{DM}	Pulsed Drain Current[2]	192	A
EAS	Single Pulse Avalanche Energy[3]	144.7	mJ
I_{AS}	Avalanche Current	53.8	A
P_D@T_C=25˚C	Total Power Dissipation[4]	62.5	W
P_D@T_A=25˚C	Total Power Dissipation[4]	4.5	W
T_{STG}	Storage Temperature Range	-55 to 150	˚C
T_J	Operating Junction Temperature Range	-55 to 150	˚C
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	62	˚C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	2.4	˚C/W

Electrical Characteristics (T_J=25℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V，I_D=250uA	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25℃，I_D=1mA	---	0.0213	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V，I_D=30A	---	4	5.5	mΩ
		V_{GS}=4.5V，I_D=15A		5.2	6	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS}，I_D =250uA	1.0	---	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient	V_{GS}=V_{DS}，I_D =250uA	---	-5.8	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V，V_{GS}=0V，T_J=25℃	---	---	1	uA
		V_{DS}=24V，V_{GS}=0V，T_J=55℃	---	---	5	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±20V，V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V，I_D=30A	---	26.5	---	S
R_g	Gate Resistance	V_{DS}=0V，V_{GS}=0V，f=1MHz	---	1.4	---	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=15V，V_{GS}=4.5V，I_D=15A	---	31.6	---	nC
Q_{gs}	Gate-Source Charge		---	8.6	---	nC
Q_{gd}	Gate-Drain Charge		---	11.7	---	nC
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V，V_{GS}=10V，R_G=3.3Ω，I_D=15A	---	9	---	ns
T_r	Rise Time		---	19	---	ns
$T_{d(off)}$	Turn-Off Delay Time		---	58	---	ns
T_f	Fall Time		---	15.2	---	ns
C_{iss}	Input Capacitance	V_{DS}=15V，V_{GS}=0V，f=1MHz	---	3075	---	pF
C_{oss}	Output Capacitance		---	400	---	pF
C_{rss}	Reverse Transfer Capacitance		---	315	---	pF
I_S	Continuous Source Current[1,6]	V_G=V_D=0V，Force Current	---	---	100	A
I_{SM}	Pulsed Source Current[2,6]		---	---	192	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V，I_S=1A，T_J=25℃	---	---	1	V

Diode Characteristics
Note；

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed，pulse width ≦ 300us，duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is VDD=25V,VGS=10V,L=0.1mH,IAS=34A
4.The power dissipation is limited by 150℃junction temperature
5 .The data is theoretically the same as ID and IDM ，in real applications，should be limited by total power dissipation.

Typical Characteristics

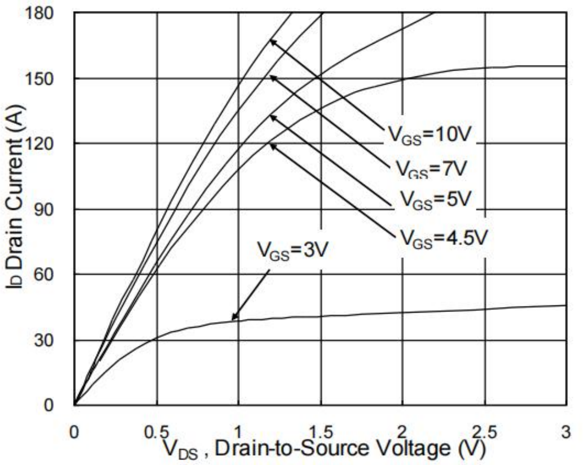


Fig.1 Typical Output Characteristics

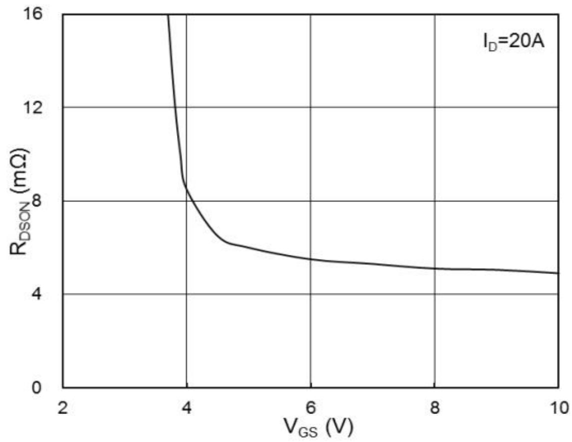


Fig.2 On-Resistance vs. G-S Voltage

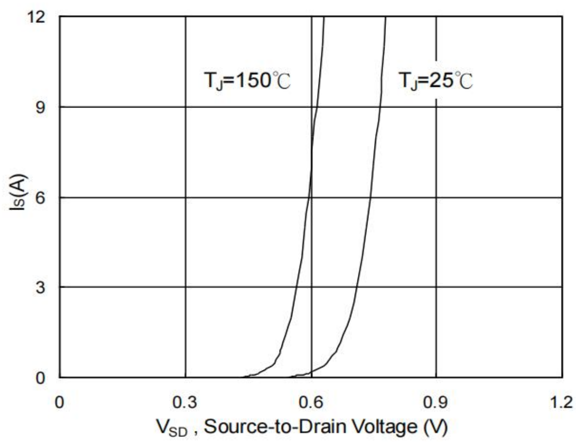


Fig.3 Forward Characteristics of Reverse

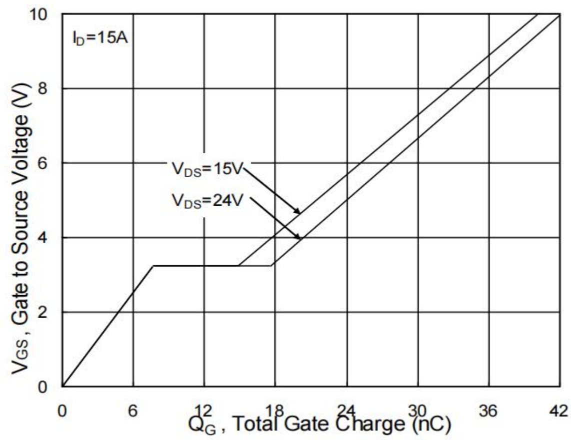


Fig.4 Gate-Charge Characteristics

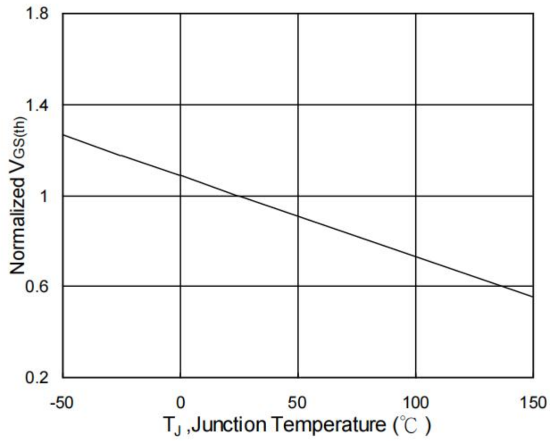


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

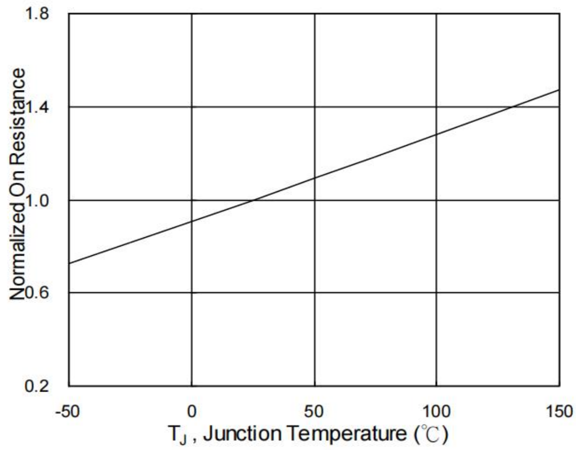


Fig.6 Normalized R_{DSON} vs. T_J

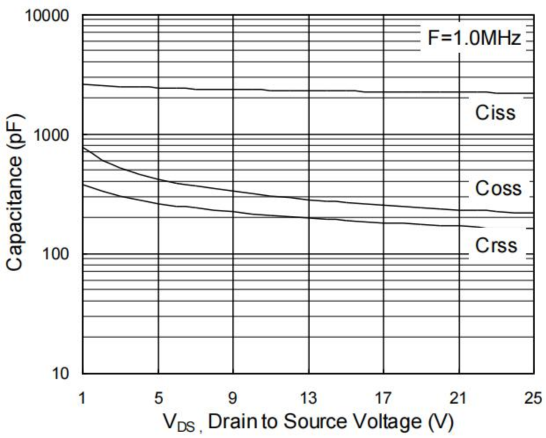


Fig.7 Capacitance

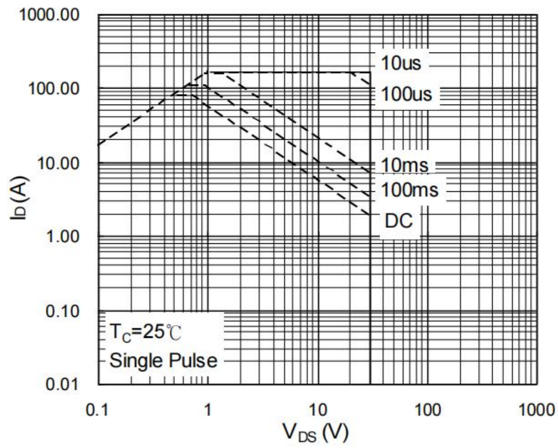


Fig.8 Safe Operating Area

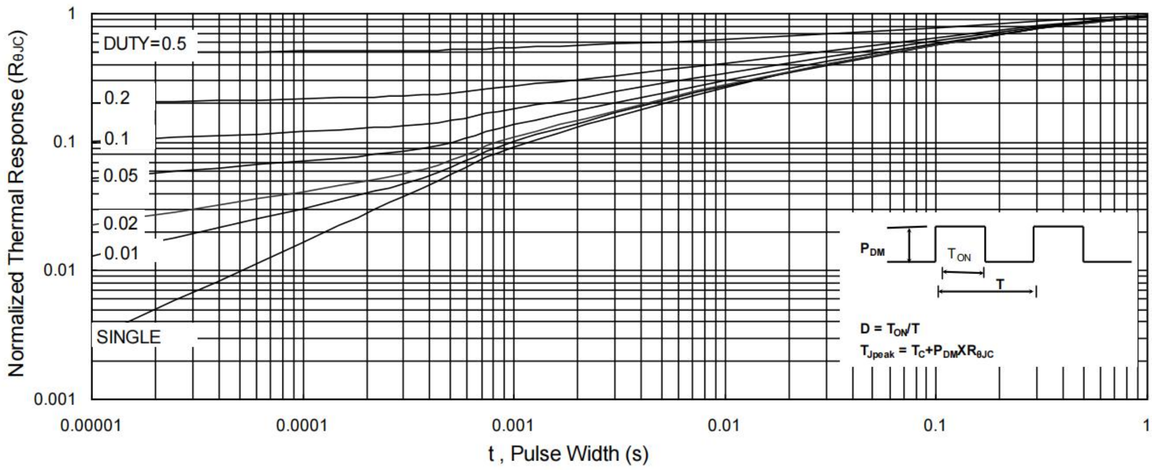


Fig.9 Normalized Maximum Transient Thermal Impedance

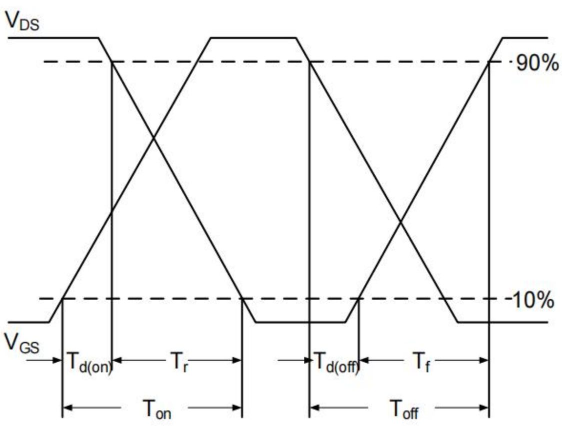


Fig.10 Switching Time Waveform

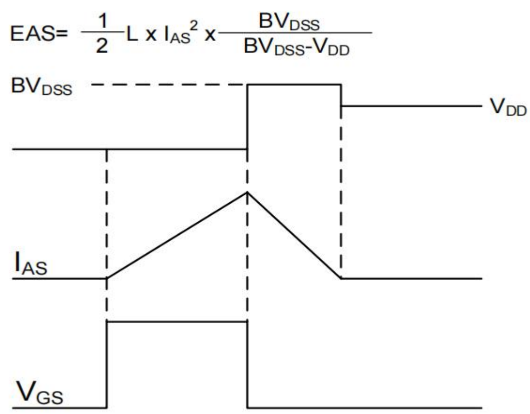
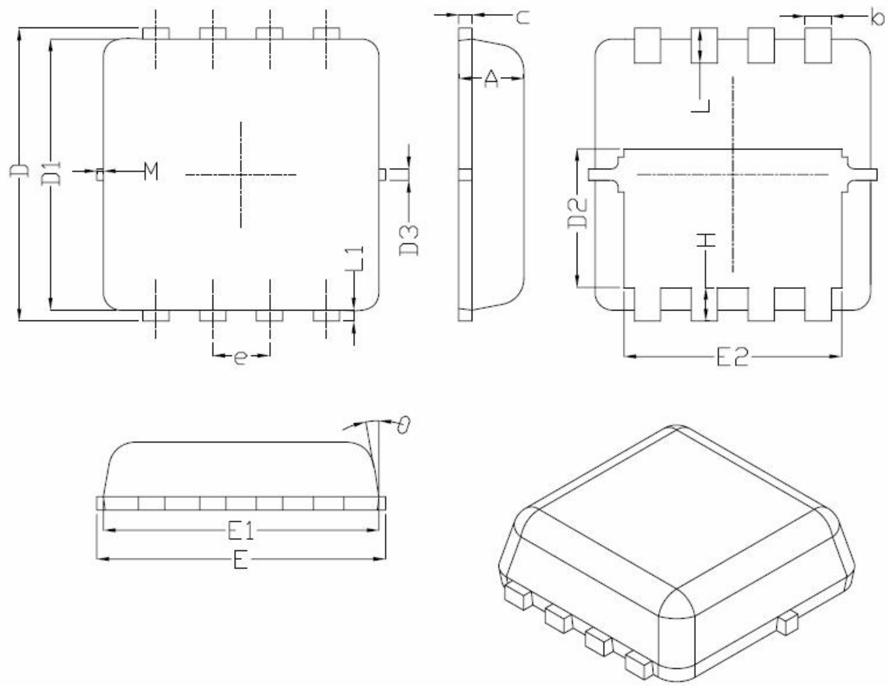


Fig.11 Unclamped Inductive Switching Waveform

DFN3X3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

REEL SPECIFICATION

P/N	PKG	QTY
AONR36366-MS	DFN3X3-8L	5000

Attention

- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specificationsof any andall MSKSEMI Semiconductor products described orcontained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer'sproducts orequipment.
- MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possiblethat these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuitsfor safedesign, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringementsof intellectual property rights or other rightsof third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.